

41. (New) The process of claim 40, wherein forming a conductive layer having a thick region comprises forming a layer of conductive material having a thick region having a width greater than other portions of the conductive layer.

42. (New) The process of claim 40, wherein forming a conductive layer having a thick region comprises forming a layer of conductive material having a thick region having a width greater than other portions of the conductive layer and a depth extending below the other portions of the conductive layer.

43. (New) The process of claim 40, wherein forming a contact comprises etching a tolerable amount of the thick region and forming a contact physically in contact with the thick region at a depth deeper than an upper surface of the thick region.

44. (New) A process for making a semiconductor device comprising:  
forming a layer of conductive material having at least one thick component;  
forming at least one contact, wherein each of the at least one contact is in contact with one of the at least one thick component.

45. (New) A process for making a semiconductor device comprising:  
forming an underlayer over a substrate;  
etching at least a portion of the underlayer to form an opening; and  
forming a conductive layer over the underlayer and forming a thick region of the conductive layer over the opening.

46. (New) The process of claim 45, further comprising:  
forming an overlayer having a thickness over the conductive layer;